

Silicon PNP Power Transistors

2SB1286

DESCRIPTION

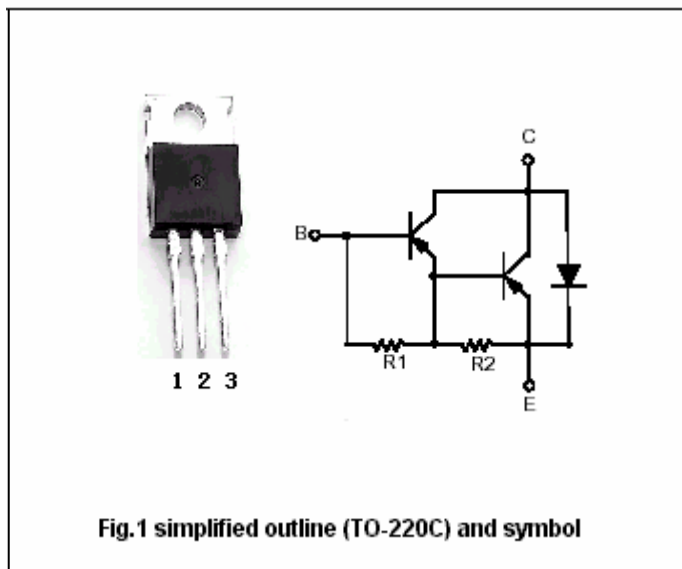
- With TO-220C package
- Complement to type 2SD1646
- DARLINGTON
- High DC current gain

APPLICATIONS

- For low frequency power amplifier and power driver applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-2	A
P _C	Collector power dissipation	T _C =25°C	25	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA, I _B =0	-100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA, I _E =0	-100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-5mA, I _C =0	-7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A, I _B =-1mA			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1A, I _B =-1mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V, I _E =0			-10	μA
I _{CEO}	Collector cut-off current	V _{CE} =-100V, I _B =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V, I _C =0			-5	mA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-2V	1000		10000	

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PACKAGE OUTLINE

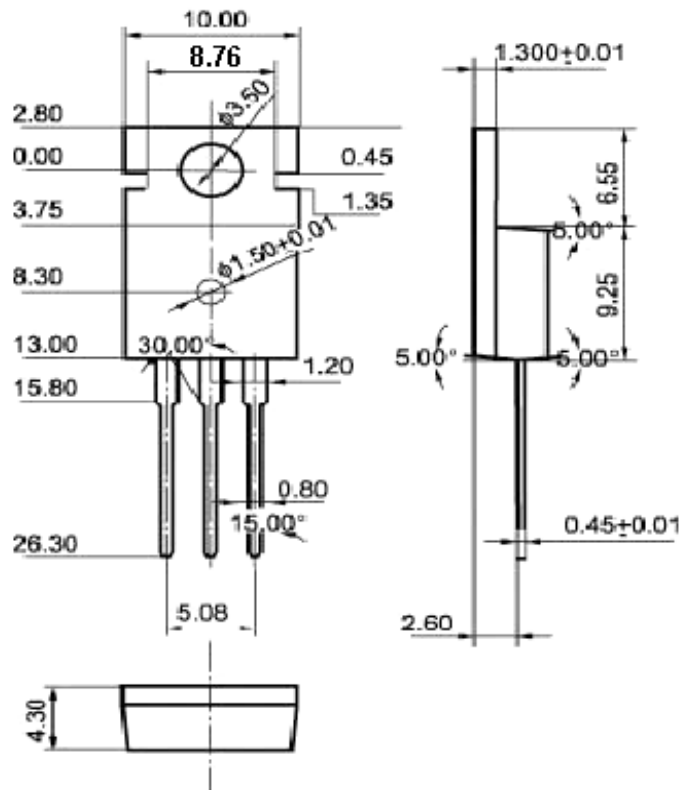


Fig.2 Outline dimensions